

Title (en)
FIELD EFFECT TRANSISTOR WITH INTEGRATED TJBS DIODE

Title (de)
FELDEFFEKTTRANSISTOR MIT INTEGRIERTER TJBS-DIODE

Title (fr)
TRANSISTOR À EFFET DE CHAMP À DIODE TJBS INTÉGRÉE

Publication
EP 2462618 A1 20120613 (DE)

Application
EP 10721527 A 20100610

Priority
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Abstract (en)
[origin: WO2011015397A1] A semiconductor component comprising at least one MOS field effect transistor and one diode is specified, wherein the diode is a trench junction barrier Schottky diode (TJBS) and the arrangement comprising MOS field effect transistor and trench junction barrier Schottky diode (TJBS) is configured as a monolithically integrated structure. The breakdown voltages of the MOS field effect transistor and of the trench junction barrier Schottky diode (TJBS) are in this case chosen in such a way that the MOS field effect transistor can be operated at breakdown.

IPC 8 full level
H01L 29/78 (2006.01)

CPC (source: EP US)
H01L 29/7806 (2013.01 - EP US); **H01L 29/7813** (2013.01 - EP US); **H01L 29/872** (2013.01 - EP US); **H01L 29/8725** (2013.01 - EP US); **H01L 21/223** (2013.01 - EP US); **H01L 29/04** (2013.01 - EP US); **H01L 29/0619** (2013.01 - EP US); **H01L 29/1095** (2013.01 - EP US); **H01L 29/41766** (2013.01 - EP US); **H01L 29/66734** (2013.01 - EP US)

Citation (search report)
See references of WO 2011015397A1

Citation (examination)
US 6049108 A 20000411 - WILLIAMS RICHARD K [US], et al

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AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

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